

High Voltage, High Current Darlington Transistor Arrays

MC1413, MC1413B, NCV1413B

The seven NPN Darlington connected transistors in these arrays are well suited for driving lamps, relays, or printer hammers in a variety of industrial and consumer applications. Their high breakdown voltage and internal suppression diodes insure freedom from problems associated with inductive loads. Peak inrush currents to 500 mA permit them to drive incandescent lamps.

The MC1413, B with a 2.7 k Ω series input resistor is well suited for systems utilizing a 5.0 V TTL or CMOS Logic.

Features

- Pb-Free Packages are Available*
- NCV Prefix for Automotive and Other Applications Requiring Site and Control Changes

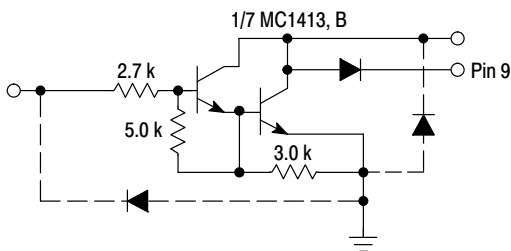


Figure 1. Representative Schematic Diagram

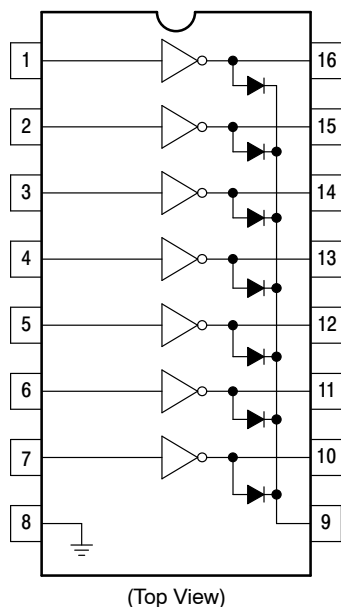
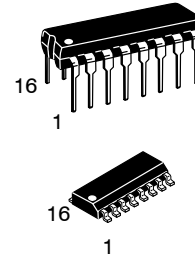


Figure 2. Pin Connections



PDIP-16
P SUFFIX
CASE 648

SOIC-16
D SUFFIX
CASE 751B

ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 5 of this data sheet.

* For additional information on our Pb-Free strategy and soldering details, please download the [onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D](#).

MC1413, MC1413B, NCV1413B

Table 1. ORDERING INFORMATION

Device	Package	Shipping [†]
MC1413DR2G	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC1413BDR2G		
NCV1413BDR2G		

DISCONTINUED (Note 1)

MC1413D	SOIC-16	48 Units / Rail
MC1413DG	SOIC-16 (Pb-Free)	48 Units / Tube
MC1413DR2	SOIC-16	2500 / Tape & Reel
MC1413P	SOIC-16	25 Units / Rail
MC1413PG	SOIC-16 (Pb-Free)	
MC1413BD	SOIC-16	48 Units / Rail
MC1413BDG	SOIC-16 (Pb-Free)	
MC1413BDR2	SOIC-16	2500 / Tape & Reel
MC1413BP	SOIC-16	25 Units / Rail
MC1413BPG	SOIC-16 (Pb-Free)	
NCV1413BDR2	SOIC-16	2500 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

1. **DISCONTINUED:** These devices are not available. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, and rating apply to any one device in the package, unless otherwise noted.)

Rating	Symbol	Value	Unit
Output Voltage	V_O	50	V
Input Voltage	V_I	30	V
Collector Current – Continuous	I_C	500	mA
Base Current – Continuous	I_B	25	mA
Operating Ambient Temperature Ranges MC1413 MC1413B NCV1413B	T_A	–20 to +85 –40 to +85 –40 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	–55 to +150	$^\circ\text{C}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient Case 648, P Suffix Case 751B, D Suffix	$R_{\theta JA}$	67 100	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case Case 648, P Suffix Case 751B, D Suffix	$R_{\theta JC}$	22 20	$^\circ\text{C/W}$
Electrostatic Discharge Sensitivity (ESD) Human Body Model (HBM) Machine Model (MM) Charged Device Model (CDM)	ESD	2000 400 1500	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



MC1413, MC1413B, NCV1413B

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
Output Leakage Current ($V_O = 50\text{ V}$, $T_A = +85\text{ }^{\circ}\text{C}$) ($V_O = 50\text{ V}$, $T_A = +25\text{ }^{\circ}\text{C}$)	All Types	I_{CEX}	–	–	100	μA
	All Types		–	–	50	
Collector–Emitter Saturation Voltage ($I_C = 350\text{ mA}$, $I_B = 500\text{ }\mu\text{A}$) ($I_C = 200\text{ mA}$, $I_B = 350\text{ }\mu\text{A}$) ($I_C = 100\text{ mA}$, $I_B = 250\text{ }\mu\text{A}$)	All Types	$V_{CE(sat)}$	–	1.1	1.6	V
	All Types		–	0.95	1.3	
	All Types		–	0.85	1.1	
Input Current – On Condition ($V_I = 3.85\text{ V}$)	MC1413, B	$I_{I(on)}$	–	0.93	1.35	mA
Input Voltage – On Condition ($V_{CE} = 2.0\text{ V}$, $I_C = 200\text{ mA}$) ($V_{CE} = 2.0\text{ V}$, $I_C = 250\text{ mA}$) ($V_{CE} = 2.0\text{ V}$, $I_C = 300\text{ mA}$)	MC1413, B	$V_{I(on)}$	–	–	2.4	V
	MC1413, B		–	–	2.7	
	MC1413, B		–	–	3.0	
Input Current – Off Condition ($I_C = 500\text{ }\mu\text{A}$, $T_A = 85\text{ }^{\circ}\text{C}$)	All Types	$I_{I(off)}$	50	100	–	μA
DC Current Gain ($V_{CE} = 2.0\text{ V}$, $I_C = 350\text{ mA}$)		h_{FE}	1000	–	–	–
Input Capacitance		C_I	–	15	30	pF
Turn-On Delay Time (50% E_I to 50% E_O)		t_{on}	–	0.25	1.0	μs
Turn-Off Delay Time (50% E_I to 50% E_O)		t_{off}	–	0.25	1.0	μs
Clamp Diode Leakage Current ($V_R = 50\text{ V}$)	$T_A = +25\text{ }^{\circ}\text{C}$	I_R	–	–	50	μA
	$T_A = +85\text{ }^{\circ}\text{C}$		–	–	100	
Clamp Diode Forward Voltage ($I_F = 350\text{ mA}$)		V_F	–	1.5	2.0	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: NCV1413B $T_{low} = -40\text{ }^{\circ}\text{C}$, $T_{high} = +125\text{ }^{\circ}\text{C}$. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.



MC1413, MC1413B, NCV1413B

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$)

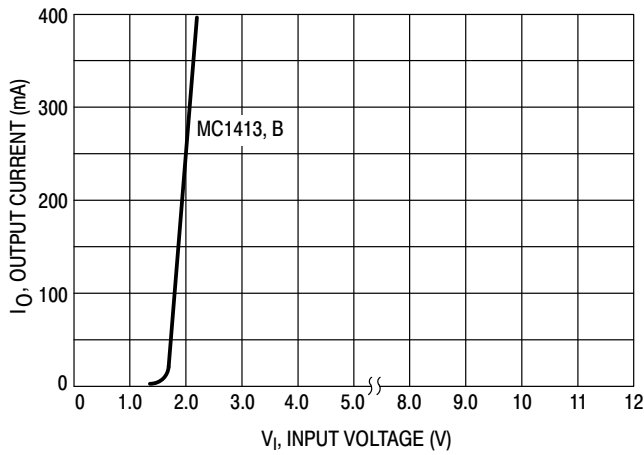


Figure 3. Output Current versus Input Voltage

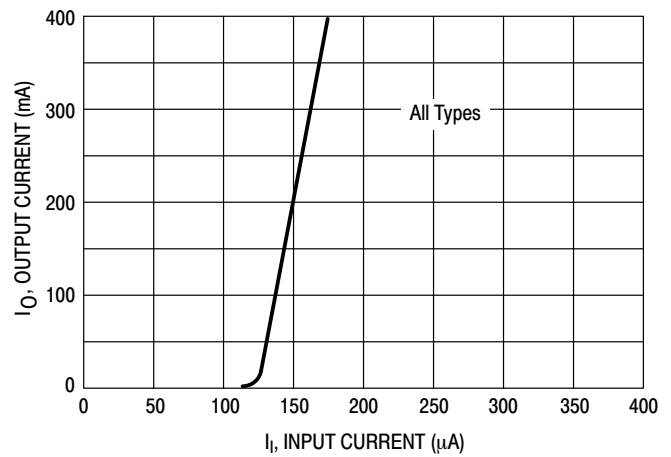


Figure 4. Output Current versus Input Current

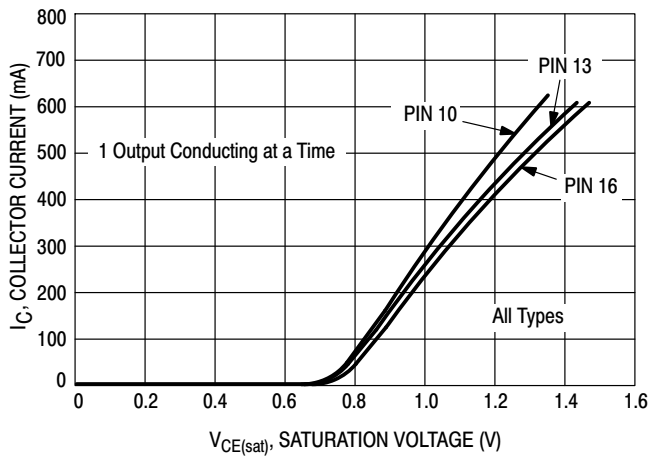


Figure 5. Typical Output Characteristics

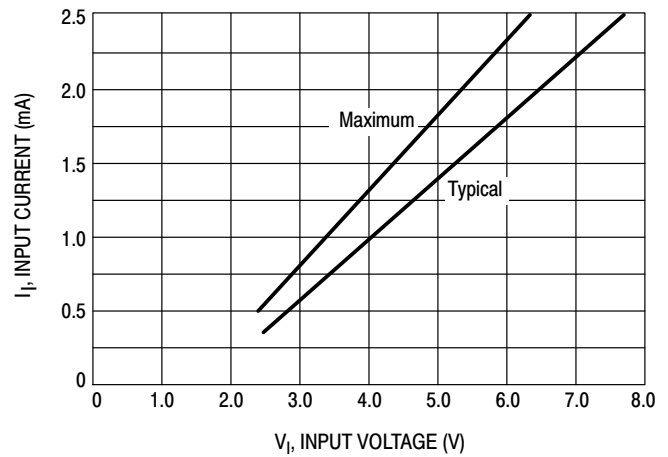


Figure 6. Input Characteristics – MC1413, B

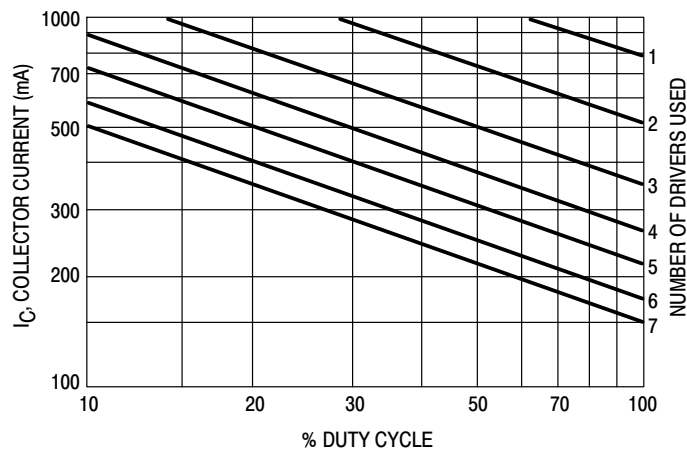
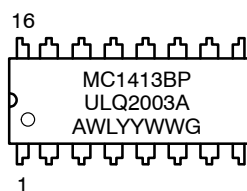
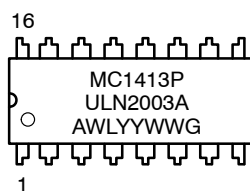


Figure 7. Maximum Collector Current
versus Duty Cycle
(and Number of Drivers in Use)

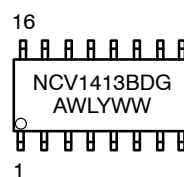
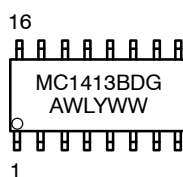
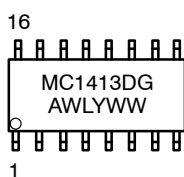
MC1413, MC1413B, NCV1413B

MARKING DIAGRAMS

PDIP-16 P SUFFIX CASE 648



SOIC-16 D SUFFIX CASE 751B



A = Assembly Location
WL = Wafer Lot
YY, Y = Year
WW = Work Week
G = Pb-Free Package

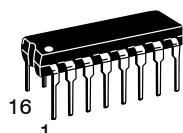
MC1413, MC1413B, NCV1413B

REVISION HISTORY

Revision	Description of Changes	Date
9	Rebranded the Data Sheet to onsemi format. MC1413D, MC1413DG, MC1413DR2, MC1413P, MC1413PG, MC1413BD, MC1413BDG, MC1413BDR2, MC1413BP, MC1413BPG, NCV1413BDR2 OPNs Marked as Discontinued.	2/25/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

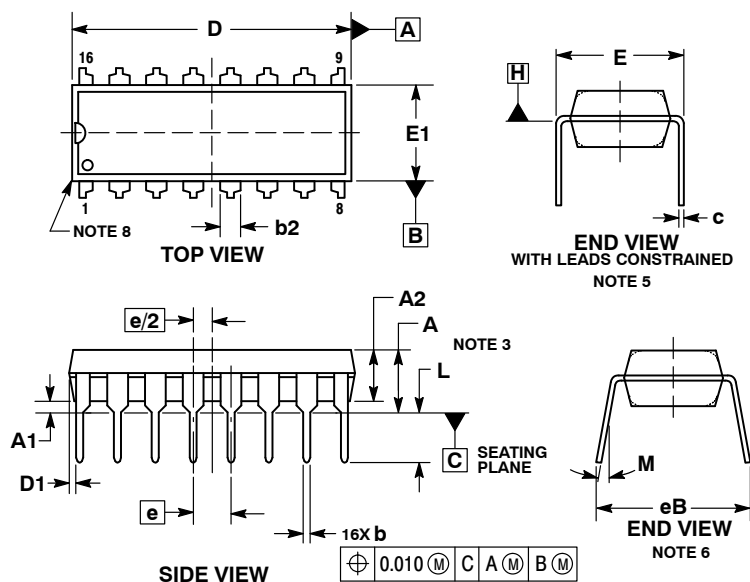




PDIP-16
CASE 648-08
ISSUE V

DATE 22 APR 2015

SCALE 1:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.015	0.210	0.38	5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
C	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
e	0.100 BSC		2.54 BSC	
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10 ⁻³		10 ⁻³

GENERIC MARKING DIAGRAM*



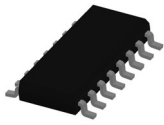
XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:	
PIN 1.	CATHODE	PIN 1.	COMMON DRAIN
2.	CATHODE	2.	COMMON DRAIN
3.	CATHODE	3.	COMMON DRAIN
4.	CATHODE	4.	COMMON DRAIN
5.	CATHODE	5.	COMMON DRAIN
6.	CATHODE	6.	COMMON DRAIN
7.	CATHODE	7.	COMMON DRAIN
8.	CATHODE	8.	COMMON DRAIN
9.	ANODE	9.	GATE
10.	ANODE	10.	SOURCE
11.	ANODE	11.	GATE
12.	ANODE	12.	SOURCE
13.	ANODE	13.	GATE
14.	ANODE	14.	SOURCE
15.	ANODE	15.	GATE
16.	ANODE	16.	SOURCE

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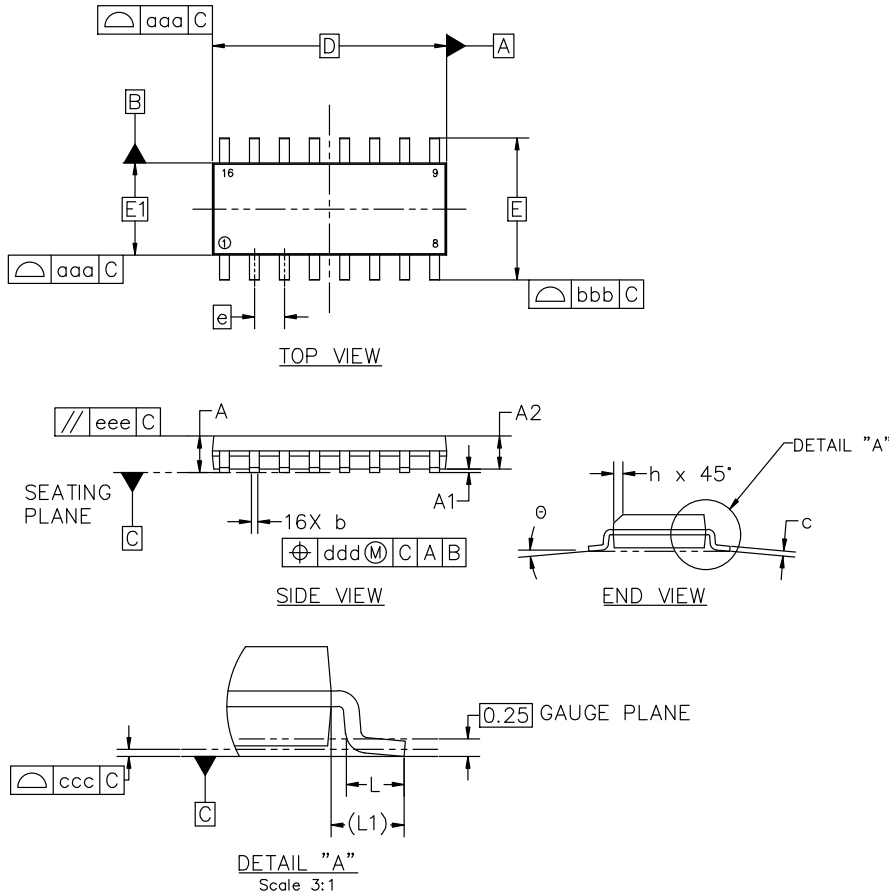
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SOIC-16 9.90x3.90x1.37 1.27P
CASE 751B
ISSUE M

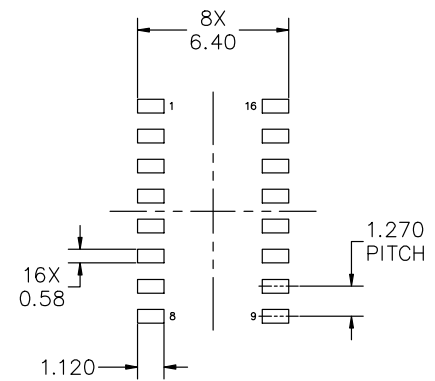
DATE 18 OCT 2024

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
5. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE b DIMENSION AT MAXIMUM MATERIAL CONDITION.



MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
A2	1.25	1.37	1.50
b	0.35	0.42	0.49
c	0.19	0.22	0.25
D	9.90 BSC		
E	6.00 BSC		
E1	3.90 BSC		
e	1.27 BSC		
h	0.25	---	0.50
L	0.40	0.83	1.25
L1	1.05 REF		
θ	0°	---	7°
TOLERANCE OF FORM AND POSITION			
aaa	0.10		
bbb	0.20		
ccc	0.10		
ddd	0.25		
eee	0.10		



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PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE onsemi SOLDERING
AND MOUNTING TECHNIQUES REFERENCE
MANUAL, SOLDERM/D

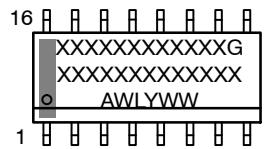
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SOIC-16 9.90x3.90x1.37 1.27P
CASE 751B
ISSUE M

DATE 18 OCT 2024

GENERIC
MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. COLLECTOR 2. BASE 3. EMITTER 4. NO CONNECTION 5. EMITTER 6. BASE 7. COLLECTOR 8. COLLECTOR 9. BASE 10. EMITTER 11. NO CONNECTION 12. EMITTER 13. BASE 14. COLLECTOR 15. EMITTER 16. COLLECTOR	STYLE 2: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION 4. CATHODE 5. CATHODE 6. NO CONNECTION 7. ANODE 8. CATHODE 9. CATHODE 10. ANODE 11. NO CONNECTION 12. CATHODE 13. CATHODE 14. NO CONNECTION 15. ANODE 16. CATHODE	STYLE 3: PIN 1. COLLECTOR, DYE #1 2. BASE, #1 3. EMITTER, #1 4. COLLECTOR, #1 5. COLLECTOR, #2 6. BASE, #2 7. EMITTER, #2 8. COLLECTOR, #2 9. COLLECTOR, #3 10. BASE, #3 11. EMITTER, #3 12. COLLECTOR, #3 13. COLLECTOR, #4 14. BASE, #4 15. EMITTER, #4 16. COLLECTOR, #4	STYLE 4: PIN 1. COLLECTOR, DYE #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. COLLECTOR, #3 6. COLLECTOR, #3 7. COLLECTOR, #4 8. COLLECTOR, #4 9. BASE, #4 10. EMITTER, #4 11. BASE, #3 12. EMITTER, #3 13. BASE, #2 14. EMITTER, #2 15. BASE, #1 16. EMITTER, #1
STYLE 5: PIN 1. DRAIN, DYE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. DRAIN, #3 6. DRAIN, #3 7. DRAIN, #4 8. DRAIN, #4 9. GATE, #4 10. SOURCE, #4 11. GATE, #3 12. SOURCE, #3 13. GATE, #2 14. SOURCE, #2 15. GATE, #1 16. SOURCE, #1	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. CATHODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE 15. ANODE 16. ANODE	STYLE 7: PIN 1. SOURCE N-CH 2. COMMON DRAIN (OUTPUT) 3. COMMON DRAIN (OUTPUT) 4. GATE P-CH 5. COMMON DRAIN (OUTPUT) 6. COMMON DRAIN (OUTPUT) 7. COMMON DRAIN (OUTPUT) 8. SOURCE P-CH 9. SOURCE P-CH 10. COMMON DRAIN (OUTPUT) 11. COMMON DRAIN (OUTPUT) 12. COMMON DRAIN (OUTPUT) 13. GATE N-CH 14. COMMON DRAIN (OUTPUT) 15. COMMON DRAIN (OUTPUT) 16. SOURCE N-CH	

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